

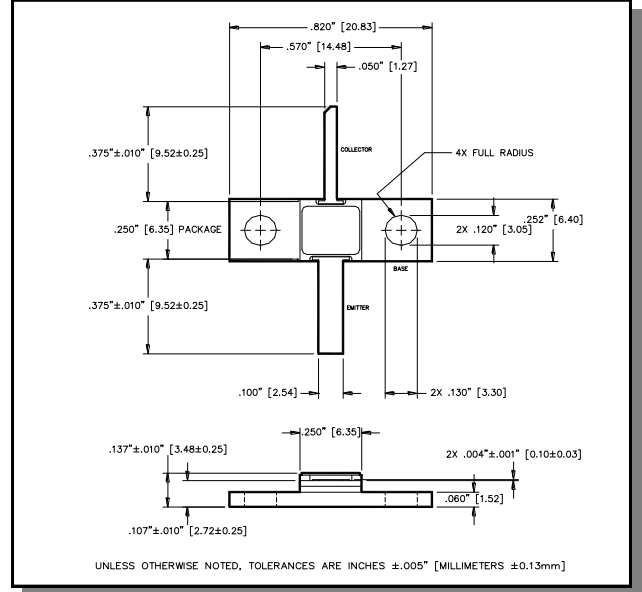
Radar Pulsed Power Transistor 25W, 1.2-1.4 GHz, 150µs Pulse, 10% Duty

Rev. V1

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	70	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	2.8	A
Power Dissipation @ +25°C	P_{TOT}	67	W
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

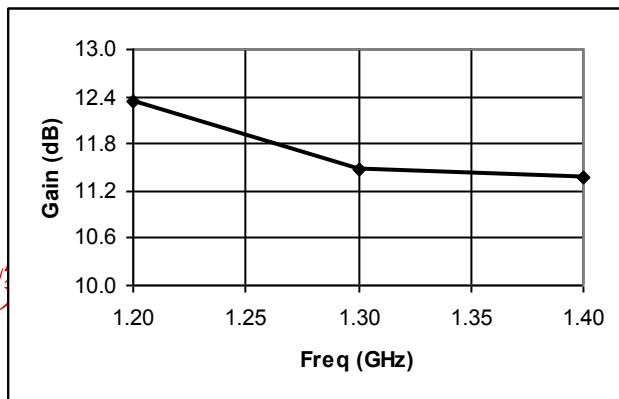
Electrical Specifications: $T_c = 25 \pm 5^\circ\text{C}$ (Room Ambient) 深圳市中立信电子科技有限公司 0755-82560215

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 25\text{mA}$		BV_{CES}	60	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40\text{V}$		I_{CES}	-	2.5	mA
Thermal Resistance	$V_{CC} = 28\text{V}$, $P_{out} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$R_{TH(JC)}$	-	2.6	°C/W
Output Power	$V_{CC} = 28\text{V}$, $P_{out} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	P_{IN}	-	2.8	W
Power Gain	$V_{CC} = 28\text{V}$, $P_{out} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	G_P	9.5	-	dB
Collector Efficiency	$V_{CC} = 28\text{V}$, $P_{out} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	η_C	50	-	%
Input Return Loss	$V_{CC} = 28\text{V}$, $P_{out} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	RL	-	-6	dB
Load Mismatch Tolerance	$V_{CC} = 28\text{V}$, $P_{out} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 28\text{V}$, $P_{out} = 25\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-S	-	1.5:1	-

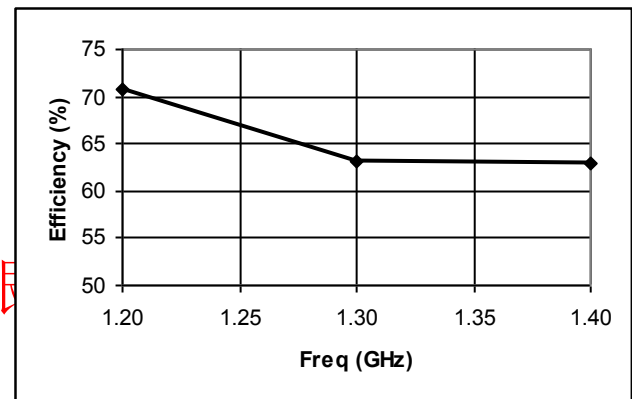
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
1.2	1.46	25	12.34	1.26	70.7	-16.5	S	P
1.3	1.78	25	11.48	1.41	63.2	-11.7	S	P
1.4	1.83	25	11.36	1.42	62.8	-8.2	S	P

Gain vs. Frequency

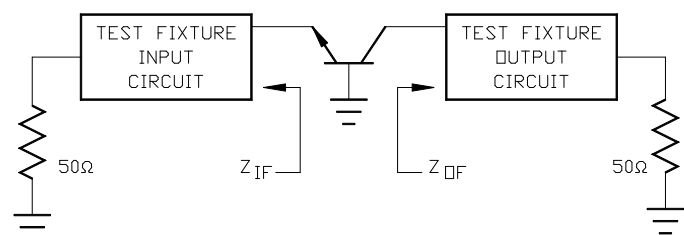


Collector Efficiency vs. Frequency



RF Test Fixture Impedance

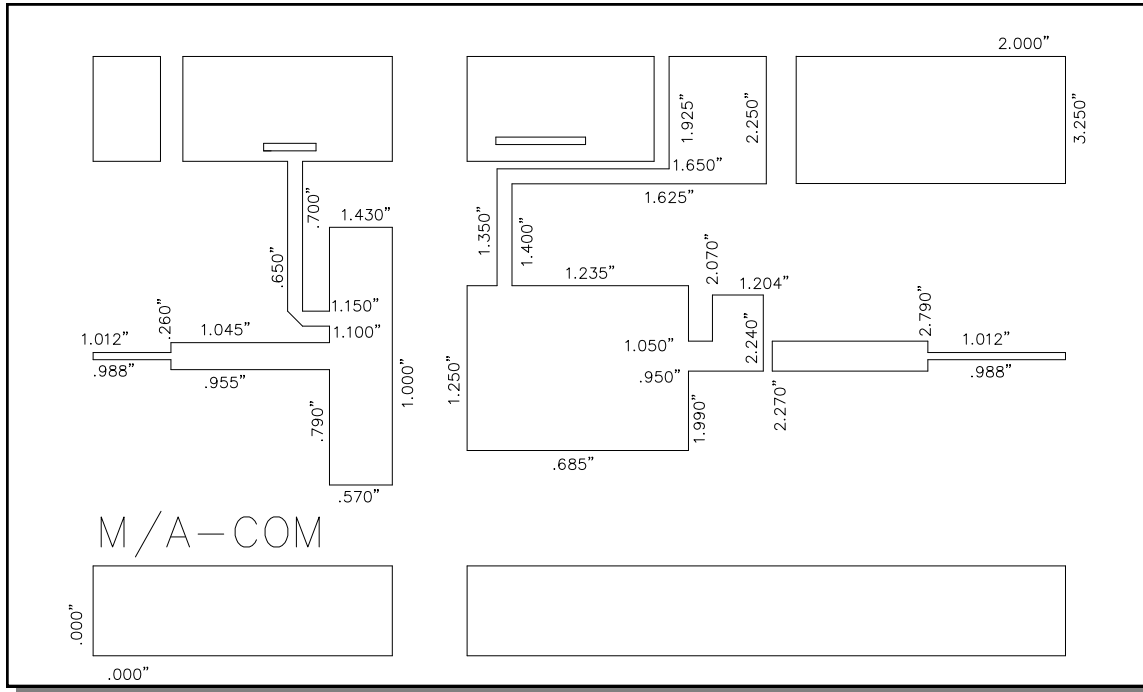
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1.2	2.1 - j4.5	3.7 + j0.9
1.3	2.1 - j3.9	3.6 + j0.4
1.4	2.2 - j3.4	3.0 + j0.2



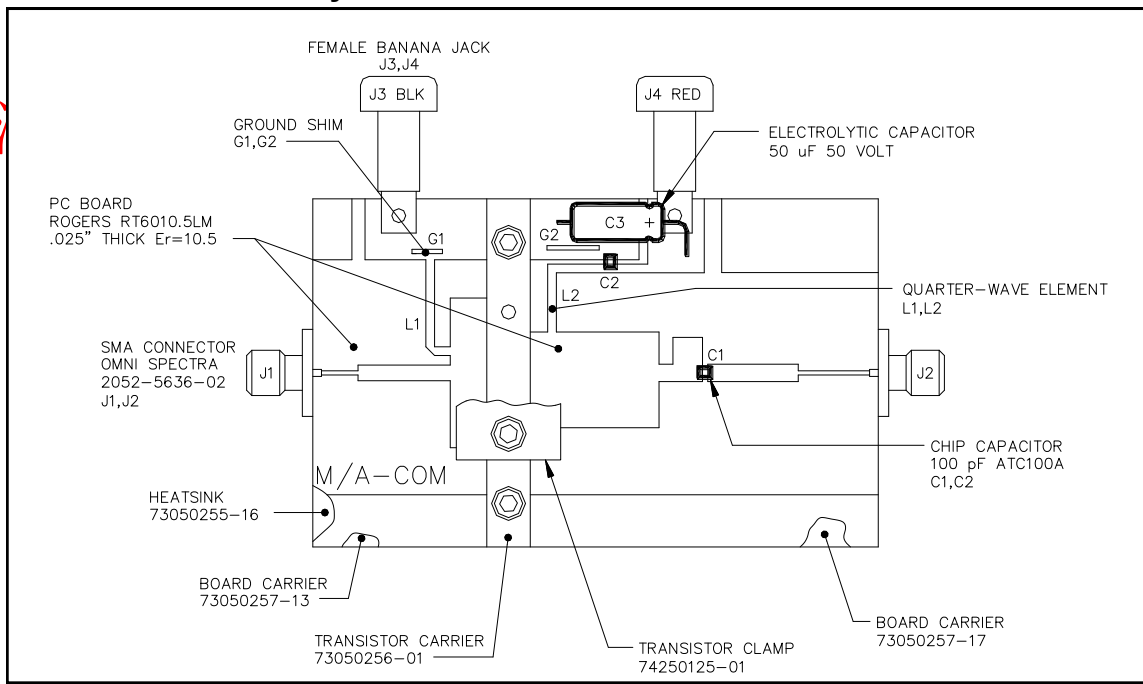
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Test Fixture Circuit Dimensions



Test Fixture Assembly



2560215

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射频功率产品

- 光电子
- 光波组件
- 放大器
- 二极管
- 网络连接解决方案
- 交叉点和信号调理器
- 频率转换
- 控制产品
- 无源器件
- SDI 产品
- 频率生成
- HDcctv 设备
- 通信处理器

应用

- 无线网络和通信
- 光网络
- 射频能量
- 工业、科学和医疗
- 有线宽带
- 广播视频
- 企业解决方案
- 监控

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